

# H7N0308LD, H7N0308LS, H7N0308LM

Silicon N Channel MOS FET  
High Speed Power Switching

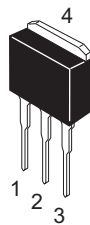
REJ03G1124-0500  
(Previous: ADE-208-1535C)  
Rev.5.00  
Apr 07, 2006

## Features

- Low on-resistance  
 $R_{DS(on)} = 3.8 \text{ m}\Omega$  typ.
- Low drive current
- 4.5 V gate drive device can be driven from 5 V source

## Outline

RENESAS Package code: PRSS0004AE-A  
(Package name: LDKPAK (L) )



H7N0308LD

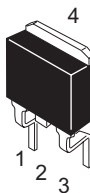
RENESAS Package code: PRSS0004AE-B  
(Package name: LDKPAK (S)-(1) )



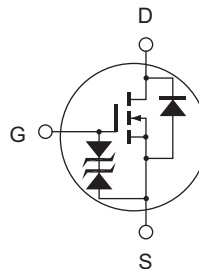
H7N0308LS

1. Gate
2. Drain
3. Source
4. Drain

RENESAS Package code: PRSS0004AE-C  
(Package name: LDKPAK (S)-(2) )



H7N0308LM



## Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Value	Unit
Drain to source voltage	V <sub>DSS</sub>	30	V
Gate to source voltage	V <sub>GSS</sub>	±20	V
Drain current	I <sub>D</sub>	70	A
Drain peak current	I <sub>D (pulse)</sub> <sup>Note 1</sup>	280	A
Body to drain diode reverse drain current	I <sub>DR</sub>	70	A
Channel dissipation	P <sub>ch</sub> <sup>Note 2</sup>	100	W
Channel to case thermal impedance	θ ch-c	1.25	°C/W
Channel to ambient thermal impedance	θ ch-a	89	°C/W
Channel temperature	T <sub>ch</sub>	150	°C
Storage temperature	T <sub>stg</sub>	-55 to +150	°C

Notes: 1. PW ≤ 10 μs, duty cycle ≤ 1%  
 2. Value at Tc = 25°C

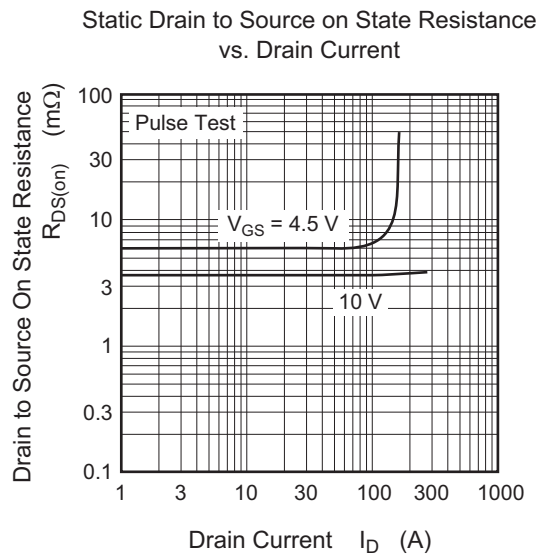
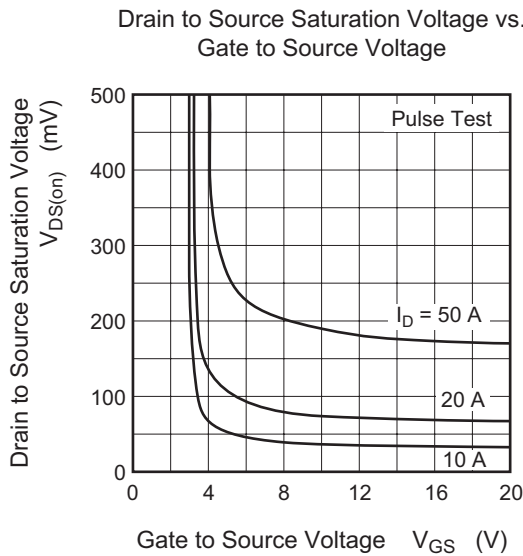
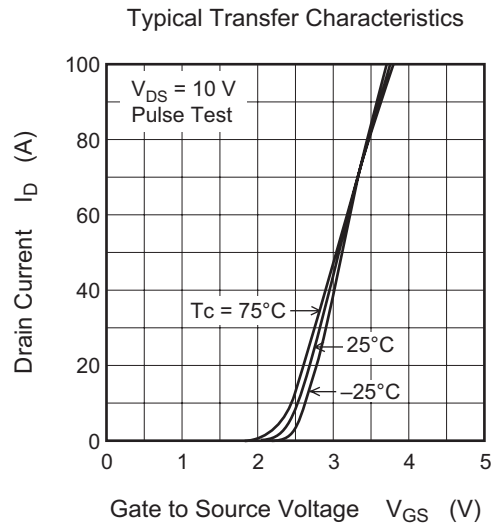
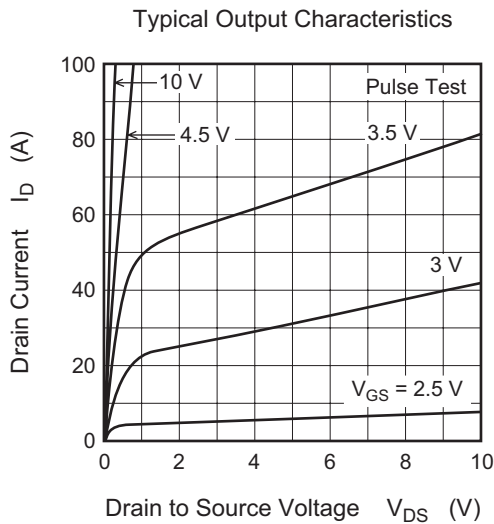
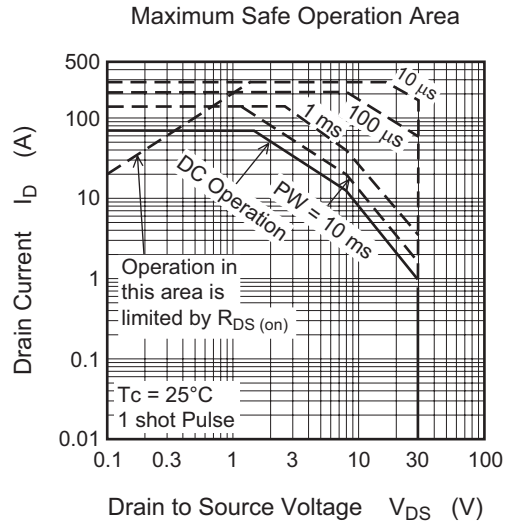
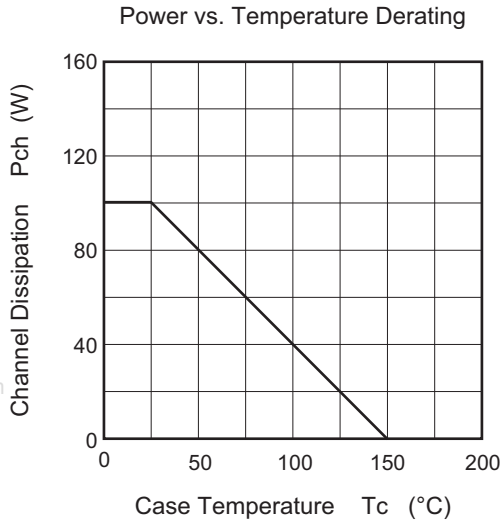
## Electrical Characteristics

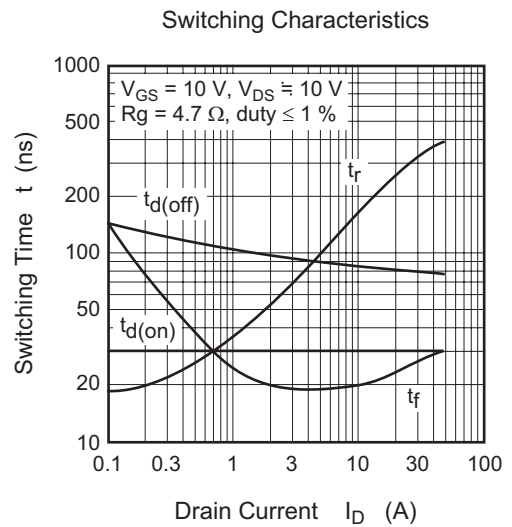
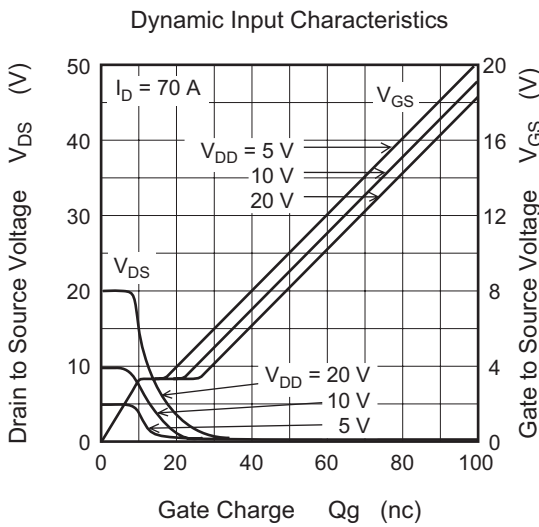
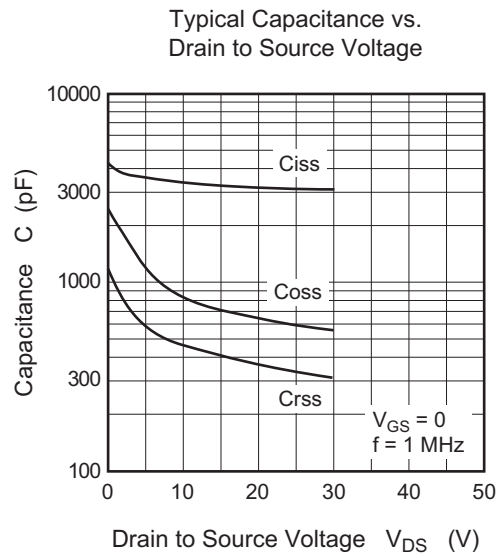
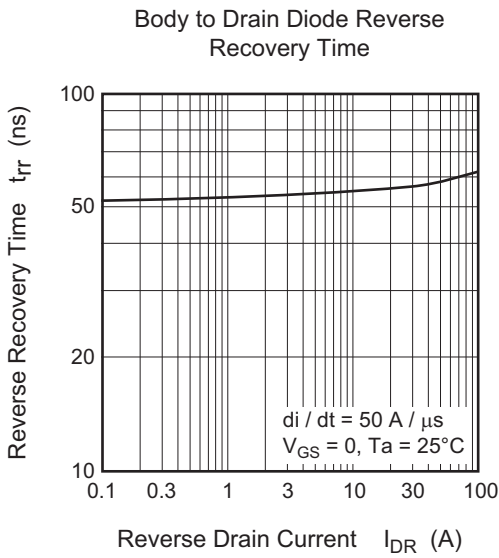
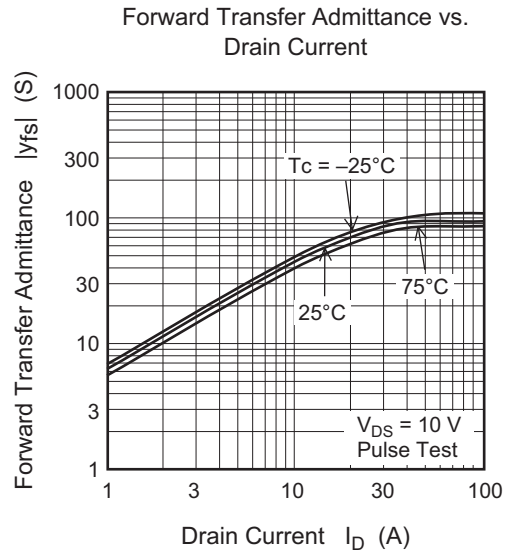
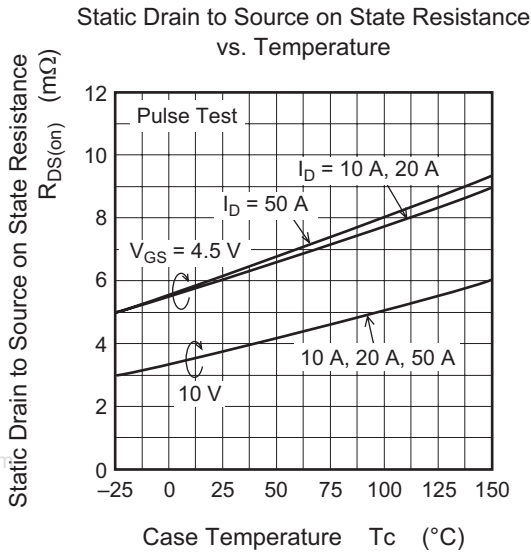
(Ta = 25°C)

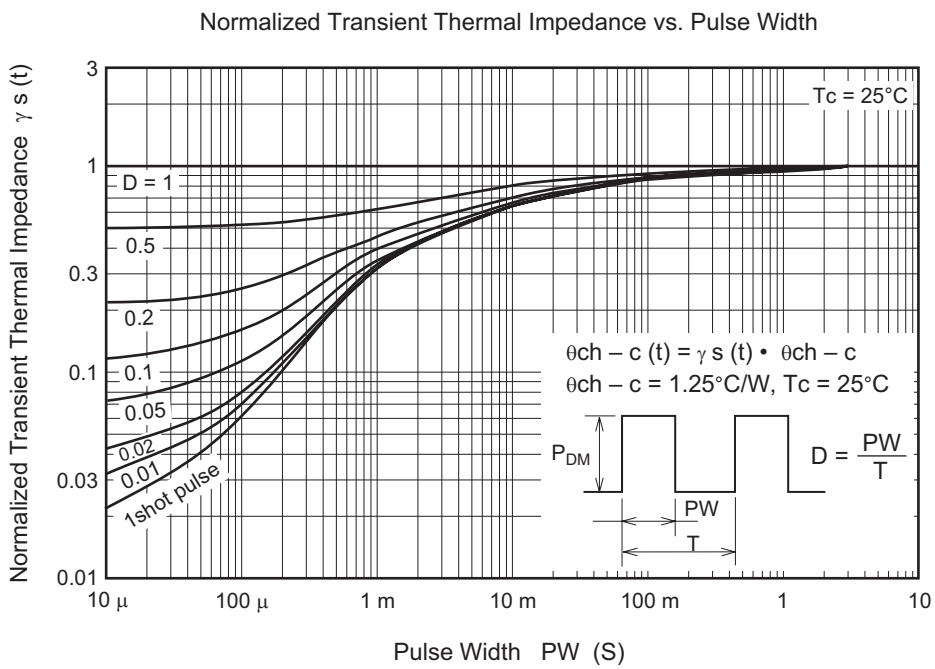
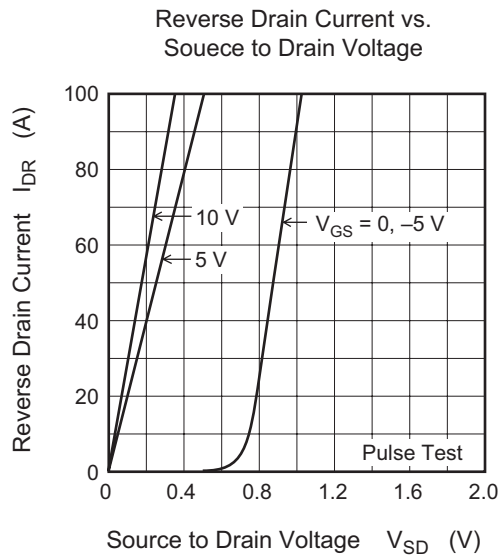
Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	V <sub>(BR) DSS</sub>	30	—	—	V	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0
Gate to source breakdown voltage	V <sub>(BR) GSS</sub>	±20	—	—	V	I <sub>G</sub> = ±100 μA, V <sub>DS</sub> = 0
Gate to source leak current	I <sub>GSS</sub>	—	—	±10	μA	V <sub>GS</sub> = ±16 V, V <sub>DS</sub> = 0
Zero gate voltage drain current	I <sub>DSS</sub>	—	—	10	μA	V <sub>DS</sub> = 30 V, V <sub>GS</sub> = 0
Gate to source cutoff voltage	V <sub>GS (off)</sub>	1.0	—	2.5	V	I <sub>D</sub> = 1 mA, V <sub>DS</sub> = 10 V <sup>Note 3</sup>
Static drain to source on state resistance	R <sub>DS (on)</sub>	—	3.8	4.8	mΩ	I <sub>D</sub> = 35 A, V <sub>GS</sub> = 10 V <sup>Note 3</sup>
		—	6.0	8.5	mΩ	I <sub>D</sub> = 35 A, V <sub>GS</sub> = 4.5 V <sup>Note 3</sup>
Forward transfer admittance	y <sub>fs</sub>	54	90	—	S	I <sub>D</sub> = 35 A, V <sub>DS</sub> = 10 V <sup>Note 3</sup>
Input capacitance	C <sub>iss</sub>	—	3350	—	pF	V <sub>DS</sub> = 10 V
Output capacitance	C <sub>oss</sub>	—	840	—	pF	V <sub>GS</sub> = 0
Reverse transfer capacitance	C <sub>rss</sub>	—	480	—	pF	f = 1 MHz
Total gate charge	Q <sub>g</sub>	—	52	—	nC	V <sub>DD</sub> = 10 V
Gate to source charge	Q <sub>gs</sub>	—	11	—	nC	V <sub>GS</sub> = 10 V
Gate to drain charge	Q <sub>gd</sub>	—	10	—	nC	I <sub>D</sub> = 70 A
Turn-on delay time	t <sub>d (on)</sub>	—	30	—	ns	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 35 A
Rise time	t <sub>r</sub>	—	370	—	ns	R <sub>L</sub> = 0.29 Ω
Turn-off delay time	t <sub>d (off)</sub>	—	80	—	ns	R <sub>g</sub> = 4.7 Ω
Fall time	t <sub>f</sub>	—	27	—	ns	
Body to drain diode forward voltage	V <sub>DF</sub>	—	0.93	—	V	I <sub>F</sub> = 70 A, V <sub>GS</sub> = 0
Body to drain diode reverse recovery time	t <sub>rr</sub>	—	60	—	ns	I <sub>F</sub> = 70 A, V <sub>GS</sub> = 0 di <sub>F</sub> /dt = 50 A/μs

Note: 3. Pulse test

Main Characteristics



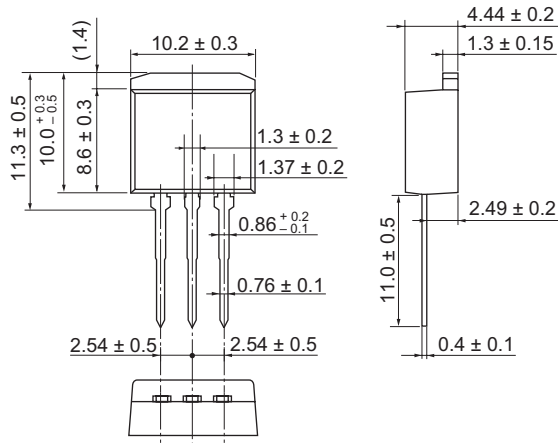




### Package Dimensions

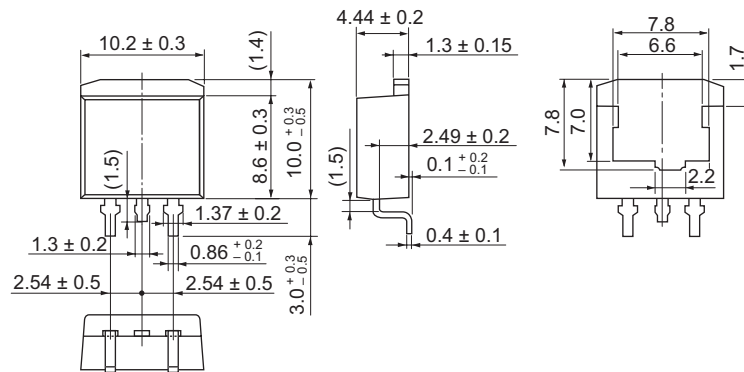
Package Name	JEITA Package Code	RENESAS Code	Previous Code	MASS[Typ.]
LDBPAK(L)	—	PRSS0004AE-A	LDBPAK(L) / LDBPAK(L)V	1.40g

Unit: mm



Package Name	JEITA Package Code	RENESAS Code	Previous Code	MASS[Typ.]
LDBPAK(S)-(1)	SC-83	PRSS0004AE-B	LDBPAK(S)-(1) / LDBPAK(S)-(1)V	1.30g

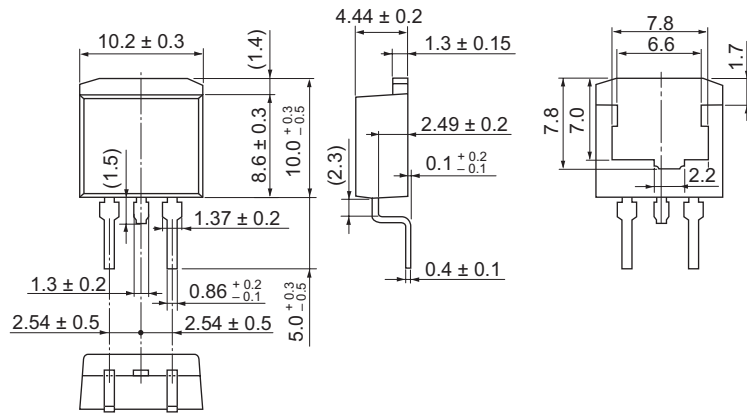
Unit: mm



# H7N0308LD, H7N0308LS, H7N0308LM

Package Name	JEITA Package Code	RENESAS Code	Previous Code	MASS[Typ.]
LDBPAK(S)-(2)	—	PRSS0004AE-C	LDBPAK(S)-(2) / LDBPAK(S)-(2)V	1.35g

Unit: mm



## Ordering Information

Part Name	Quantity	Shipping Container
H7N0308LD-E	500 pcs	Box (Conductive Sack)
H7N0308LSTL-E	1000 pcs	Taping
H7N0308LMTL-E	1000 pcs	Taping

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.

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